

60 V, 300 mA dual N-channel Trench MOSFET

Rev. 2 — 23 September 2010

**Product data sheet** 

### 1. Product profile

#### 1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### **1.2 Features and benefits**

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

#### **1.3 Applications**

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

#### Table 1.Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	$T_{amb} = 25 \ ^{\circ}C$	-	-	60	V
V <sub>GS</sub>	gate-source voltage	T <sub>amb</sub> = 25 °C	-	-	±20	V
I <sub>D</sub>	drain current	$T_{amb} = 25 \text{ °C};$ $V_{GS} = 10 \text{ V}$	<u>[1]</u> -	-	300	mA
R <sub>DSon</sub>	drain-source on-state resistance	T <sub>j</sub> = 25 °C; V <sub>GS</sub> = 10 V; I <sub>D</sub> = 500 mA	-	1	1.6	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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### 2. Pinning information

Table 2.	Pinning			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		
2	G1	gate 1		
3	D2	drain 2		
4	S2	source 2		
5	G2	gate 2	<u> </u> 1   2   3	2 5
6	D1	drain 1		

017aaa055

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### 3. Ordering information

Table 3. Ord	lering infor	mation	
Type number	Package		
	Name	Description	Version
2N7002BKS	SC-88	plastic surface-mounted package; 6 leads	SOT363

#### 4. Marking

Table 4. N	larking codes	
Type numbe	r	Marking code <sup>[1]</sup>
2N7002BKS		ZT*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

			,		
Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	sistor				
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C	-	60	V
$V_{GS}$	gate-source voltage	T <sub>amb</sub> = 25 °C	-	±20	V
I <sub>D</sub> drain current	drain current	V <sub>GS</sub> = 10 V	<u>[1]</u>		
	T <sub>amb</sub> = 25 °C	-	300	mA	
		T <sub>amb</sub> = 100 °C	-	215	mA

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Symbol	Parameter	Conditions	Min	Max	Unit
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$	-	1.2	А
P <sub>tot</sub> total powe	total power dissipation	T <sub>amb</sub> = 25 °C	[2] _	295	mW
			<u>[1]</u> _	340	mW
		T <sub>sp</sub> = 25 °C	-	1040	mW
Source-d	rain diode				
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u> _	300	mA
ESD max	imum rating				
V <sub>ESD</sub>	electrostatic discharge voltage	human body model	<u>[3]</u> _	2000	V
Per devic	e				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2] _	445	mW
Tj	junction temperature			150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

Table 5. Limiting values ... continued

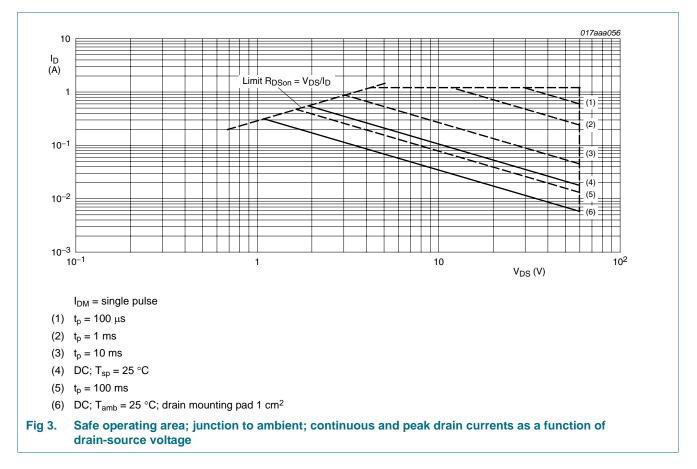
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard [2] footprint.

- 017aaa001 017aaa002 120 120 P<sub>der</sub> (%) l<sub>der</sub> (%) 80 80 40 40 0 0 125 175 T<sub>amb</sub> (°C) 125 175 T<sub>amb</sub> (°C) \_75 -25 25 75 -75 -25 25 75  $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$  $I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \ \%$ Normalized total power dissipation as a Fig 2. Normalized continuous drain current as a Fig 1. function of ambient temperature function of ambient temperature
- [3] Measured between all pins.

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#### 6. Thermal characteristics

#### Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	<u>[1]</u> -	370	425	K/W
		[2] _	320	370	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	120	K/W
Per device	)					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	275	K/W

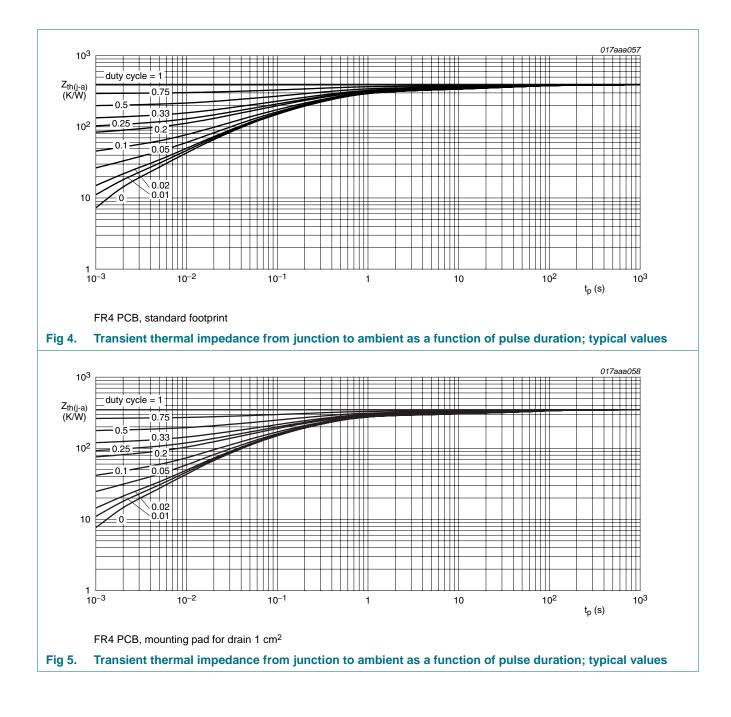
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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### 7. Characteristics

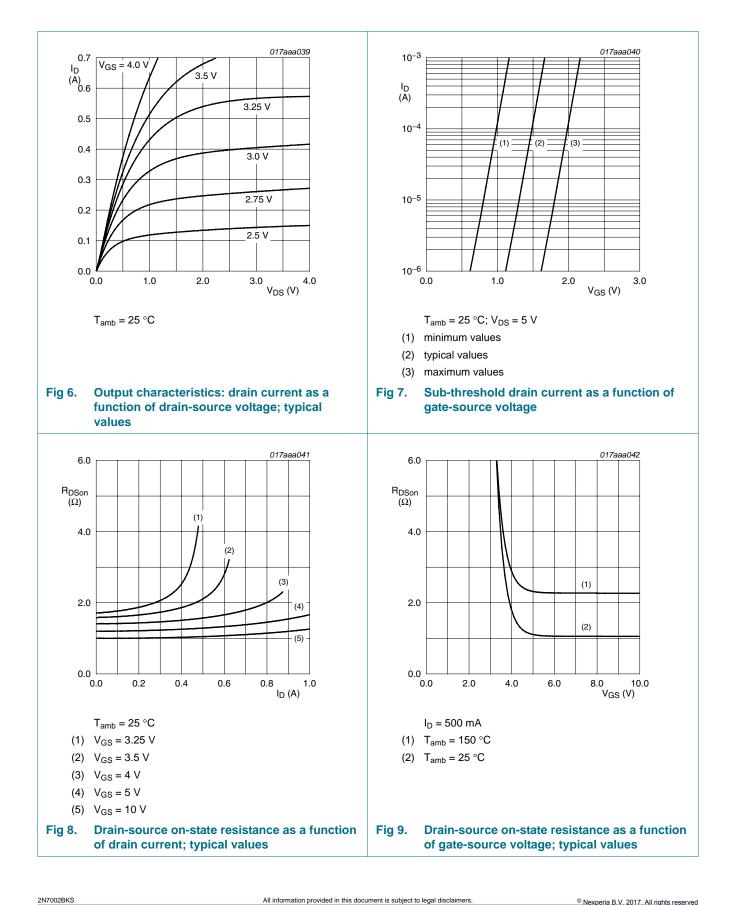
<b>Table 7.</b> <i>T<sub>j</sub></i> = 25 <i>°</i> C √	Characteristics unless otherwise specified.					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 10 \ \mu\text{A}; \ V_{GS} = 0 \ V$	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}$	1.1	1.6	2.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T <sub>j</sub> = 25 °C	-	-	1	μΑ
		T <sub>j</sub> = 150 °C	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = ±20 V; $V_{DS}$ = 0 V	-	-	10	μA
Dooli	drain-source on-state		<u>[1]</u>			
	resistance	$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 50 \text{ mA}$	-	1.3	2	Ω
		$V_{GS}$ = 10 V; I <sub>D</sub> = 500 mA	-	1	1.6	Ω
<b>g</b> <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; I <sub>D</sub> = 200 mA	<u>[1]</u>	550	-	mS
Dynamic of	characteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 300 mA;	-	0.5	0.6	nC
$Q_{GS}$	gate-source charge	<sup>−</sup> V <sub>DS</sub> = 30 V; - V <sub>GS</sub> = 4.5 V	-	0.2	-	nC
Q <sub>GD</sub>	gate-drain charge	$-v_{GS} = 4.5 v$	-	0.1	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 10 V;$	-	33	50	pF
C <sub>oss</sub>	output capacitance	f = 1 MHz	-	7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DD</sub> = 50 V;	-	5	10	ns
t <sub>r</sub>	rise time	R <sub>L</sub> = 250 Ω; - V <sub>GS</sub> = 10 V;	-	6	-	ns
t <sub>d(off)</sub>	turn-off delay time	$-v_{GS} = 10 v,$ $R_G = 6 \Omega$	-	12	24	ns
t <sub>f</sub>	fall time		-	7	-	ns
Source-dr	ain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 115 mA; V <sub>GS</sub> = 0 V	0.47	0.75	1.1	V

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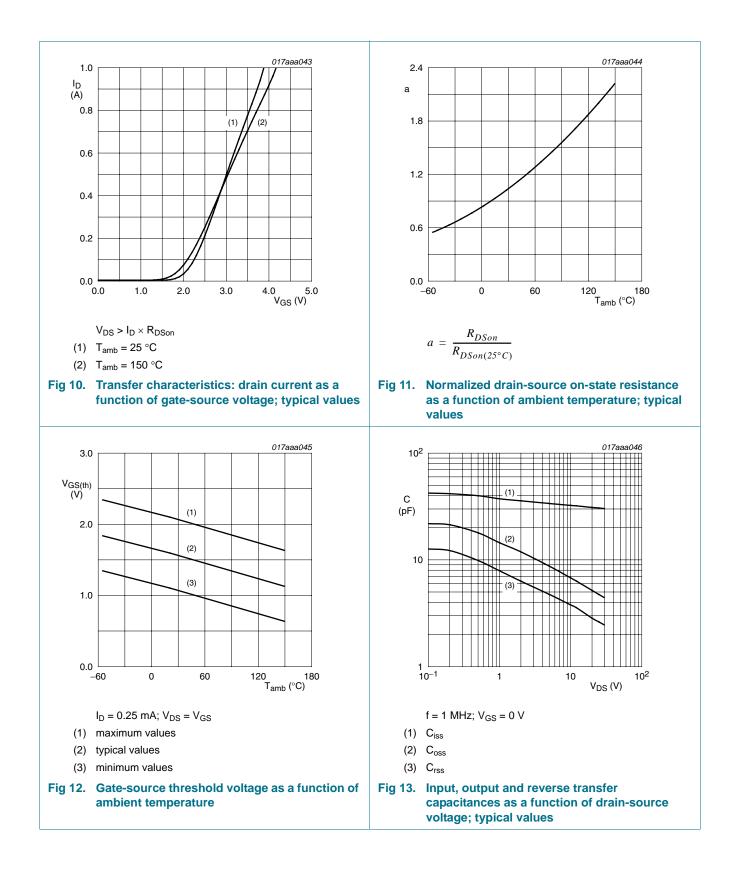
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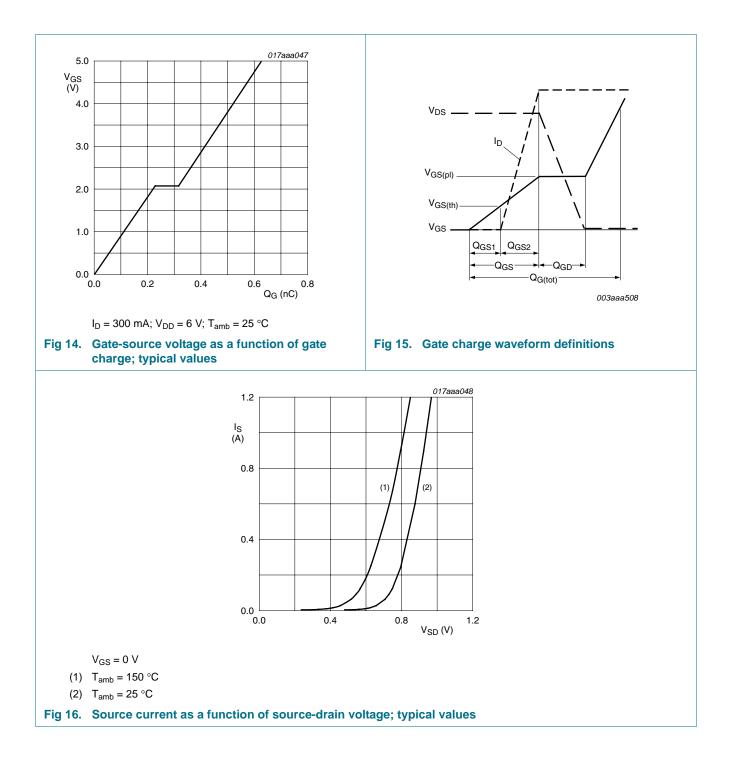
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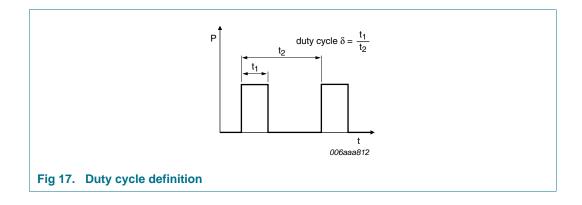
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#### 60 V, 300 mA dual N-channel Trench MOSFET



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### 8. Test information



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### 9. Package outline

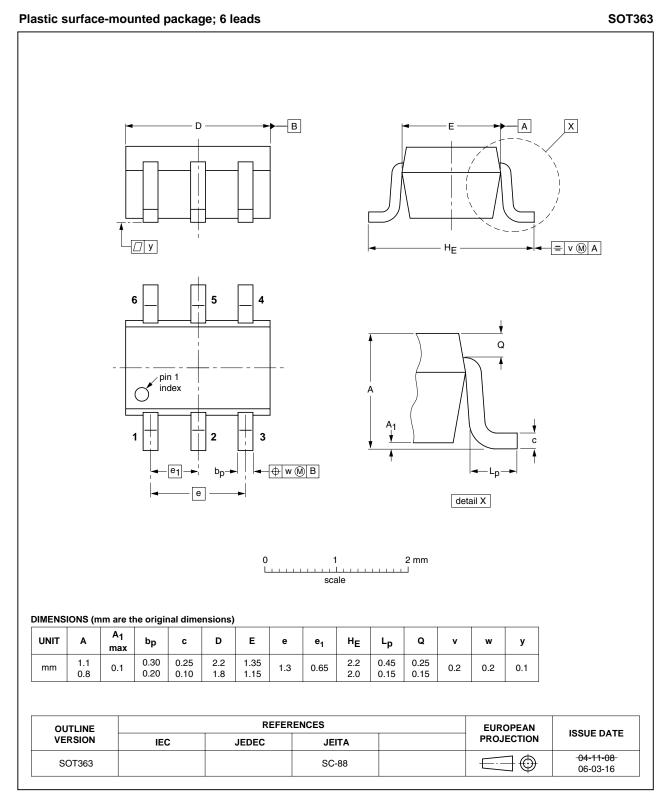
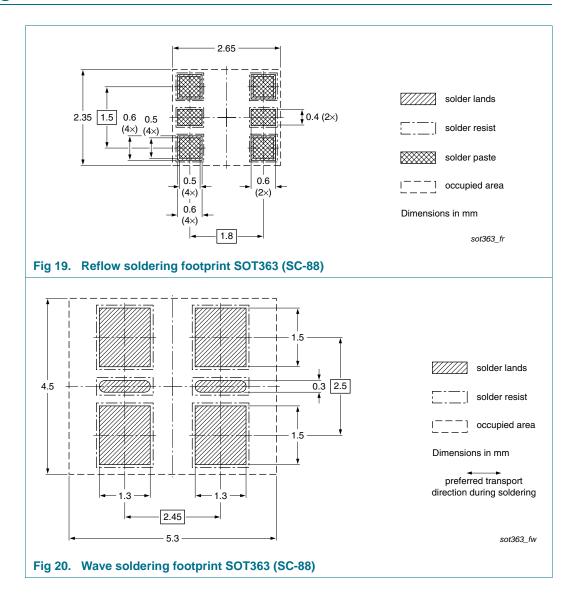


Fig 18. Package outline SOT363 (SC-88)

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### **10. Soldering**



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### **11. Revision history**

Table 8. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
2N7002BKS v.2	20100923	Product data sheet	-	2N7002BKS v.1
Modifications:	• Table 2 "Pin	ning": graphic symbol ame	nded	
2N7002BKS v.1	20100617	Product data sheet	-	-

#### 60 V, 300 mA dual N-channel Trench MOSFET

### **12. Legal information**

#### 12.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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